BATOP optoelectronics

SAM™ Data Sheet SAM-1030-30-1ps-x, λ = 1030 nm

Laser wavelength	λ = 1030 nm
High reflection band (R > 50%)	λ = 970 .. 1060 nm
Absorbance	A_0 = 30 %
Modulation depth	ΔR = 18 %
Non-saturable loss	A_{ns} = 12 %
Saturation fluence	Φ_{sat} = 40 µJ/cm^2
Relaxation time constant	τ ~ 1 ps
Damage threshold	Φ = 800 µJ/cm^2
Chip area	4.0 mm x 4.0 mm; other dimensions on request
Chip thickness	450 µm;
Protection	the SAM is protected with a dielectric front layer

Mounting option **x** denotes the type of mounting as follows:

x = 0	unmounted
x = 12.7 g	glued on a gold plated Cu-cylinder with 12.7 mm ∅
x = 25.4 g	glued on a gold plated Cu-cylinder with 25.4 mm ∅
x = 12.7 s	soldered on a gold plated Cu-cylinder with 12.7 mm ∅
x = 25.4 s	soldered on a gold plated Cu-cylinder with 25.4 mm ∅
x = FC	mounted on a 1 m monomode fiber cable with FC connector

Low intensity spectral reflectance